

Oral Presentation

[AMD1]Foldable Technology of OLED Displays

Chair: Koichi Miwa (LG Display Co.,Ltd)

Co-Chair: Keisuke Omoto (Apple)

Wed. Nov 27, 2019 1:40 PM - 3:15 PM Mid-sized Hall B (1F)

2:55 PM - 3:15 PM

[AMD1-4]Positive Bias-Stress Stability of Flexible Amorphous InGaZnO Thin Film Transistors with Double-Stacked Gate Insulators

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Keywords:flexible, a-IGZO TFT, Double-stacked Gate Insulator, PBS

Double-stacked gate insulators (SiO_x/TaO_x) made flexible amorphous InGaZnO thin film transistors more stable under both mechanical bending and positive bias-stress, which was assumed to result from their better neutral plane position and front-channel interface states. A simple model was built to explain this improvement effect.